

In the Drawings

Please delete sheets numbered 1/12, 7/12, and 8/12 containing Figures 1A-1B, 7 and 8, respectively, and insert attached Replacement Sheets 1, 7 and 8.

REMARKS

Claims 2-15 and 20 remain pending in the application with the present amendments. Claim 20 stands withdrawn as having not been elected in response to a prior restriction requirement. Claim 1 is canceled in favor of amended claim 15, from which all of claims 2-14 ultimately depend.

The objections to Figure 1A and claim 2 have been addressed herein by their amendment.

In addition, the specification and Figures 7 and 8 of the drawings are amended herein to add reference signs to features which appear in the original Figures and are supported by the original drawings and specification but were not specifically referenced before. A set of Replacement Sheets are submitted herewith together with a set of Annotated Sheets showing the changes made to the drawings. The specification is also amended accordingly. It is respectfully submitted that no new matter is contained in the present amendments.

In the Office Action, the Examiner rejected all of the previously pending claims under 35 U.S.C. §103(a) as being obvious over U.S. Patent No. 6,316,302 to Cheek et al. ("Cheek") in view of U.S. Patent Publication No. 2002/0197806 to Furukawa et al. ("Furukawa") or in view of U.S. Patent No. 6,855,988 to Madurawe ("Madurawe"). For the reasons set forth below, applicants submit that the claims as amended herein overcome the rejections. Reconsideration and allowance is respectfully requested.

As amended herein, claim 15 now specifies that the first spacers have an "L" shape. Being "L"-shaped, as shown in Figure 7 and as described in the specification, each first spacer includes a vertically extending portion oriented in a vertical direction,

i.e., a direction generally perpendicular to the main surface of a substrate. Each first spacer also includes a horizontally extending portion which is oriented in a horizontal direction parallel to the main surface of the substrate. In addition, the horizontally extending portion has an edge which is horizontally displaced from a wall of the vertically extending portion. Second spacers are formed which extend along walls of the vertically extending portions and which overlie the horizontally extending portions of the first spacers.

With the first and second spacers in place, source and drain regions of a first FET (e.g., a PFET - claim 2) are implanted, aligned to the edges of the horizontally extending portions of the first spacers.

The second spacers are then removed, as well as the horizontally extending portions of the first spacers, but leaving the vertically extending portions of the L-shaped first spacers in place. Thus, only part of the first spacers are removed during this step. Source and drain regions of a second FET (e.g., an NFET - claim 2) are then implanted, aligned to the walls of the vertically extending portions of the first spacers.

The recited method results in the source and drain regions of the first transistor being aligned with edges of the horizontal portions of the L-shaped spacers, and the source and drain regions of the second transistor being aligned with the walls of the vertical portions of the same spacers, that is, the remaining parts of the original L-shaped spacers.

It is respectfully submitted that these features are neither taught nor suggested by the art cited by the Examiner to reject the claims. Clearly, *Cheek* neither teaches nor suggests forming L-shaped spacers, implanting source and drain regions of one

transistor aligned to the horizontal edges of the horizontal portions of the L-shaped spacers, then removing the horizontal portions of the L-shaped spacers and implanting source and drain regions of another transistor aligned to the walls of the remaining vertical portions of the L-shaped spacers. *Cheek* merely describes removal of one entire spacer between source and drain implants of respective transistors. Moreover, neither *Furukawa* nor *Madurawe* provides the teachings which *Cheek* lacks with respect to the invention recited in the presently pending claims. Neither *Furukawa* nor *Madurawe* teaches or suggests forming L-shaped spacers, implanting source and drain regions of one transistor aligned to the horizontal edges of the horizontal portions of the L-shaped spacers, then removing the horizontal portions of the L-shaped spacers and implanting source and drain regions of another transistor aligned to the walls of the remaining vertical portions of the L-shaped spacers.

Support for the amendments to the claims is provided, *inter alia* in the original Figures and the content of the originally filed specification, and specific support is found in the language of the specification as amended at pp. 10-12.

Accordingly, in view of the amendments and remarks herein, it is believed that all claims of the application are now in condition for allowance. However, if for any reason the Examiner does not believe that such action can be taken at this time, the Examiner is requested to telephone the Applicants' attorney at the number indicated below to discuss any issues that may remain.

It is believed that no fee is due in connection with the filing of this Amendment. However, if any fee is due, authorization is granted to debit the Deposit Account No. 09-0458 of the Assignee. If there is an overpayment, please credit the same account.

Respectfully submitted,
Rainer E. Gehres et al.

By:

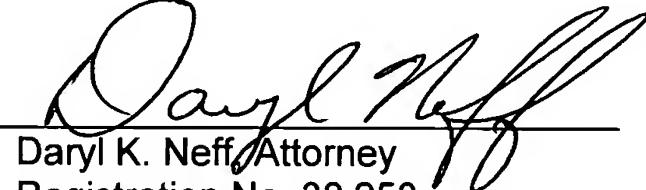

Daryl K. Neff, Attorney
Registration No. 38,253
Telephone: (973) 316-2612



Figure 1A
(PRIOR ART)

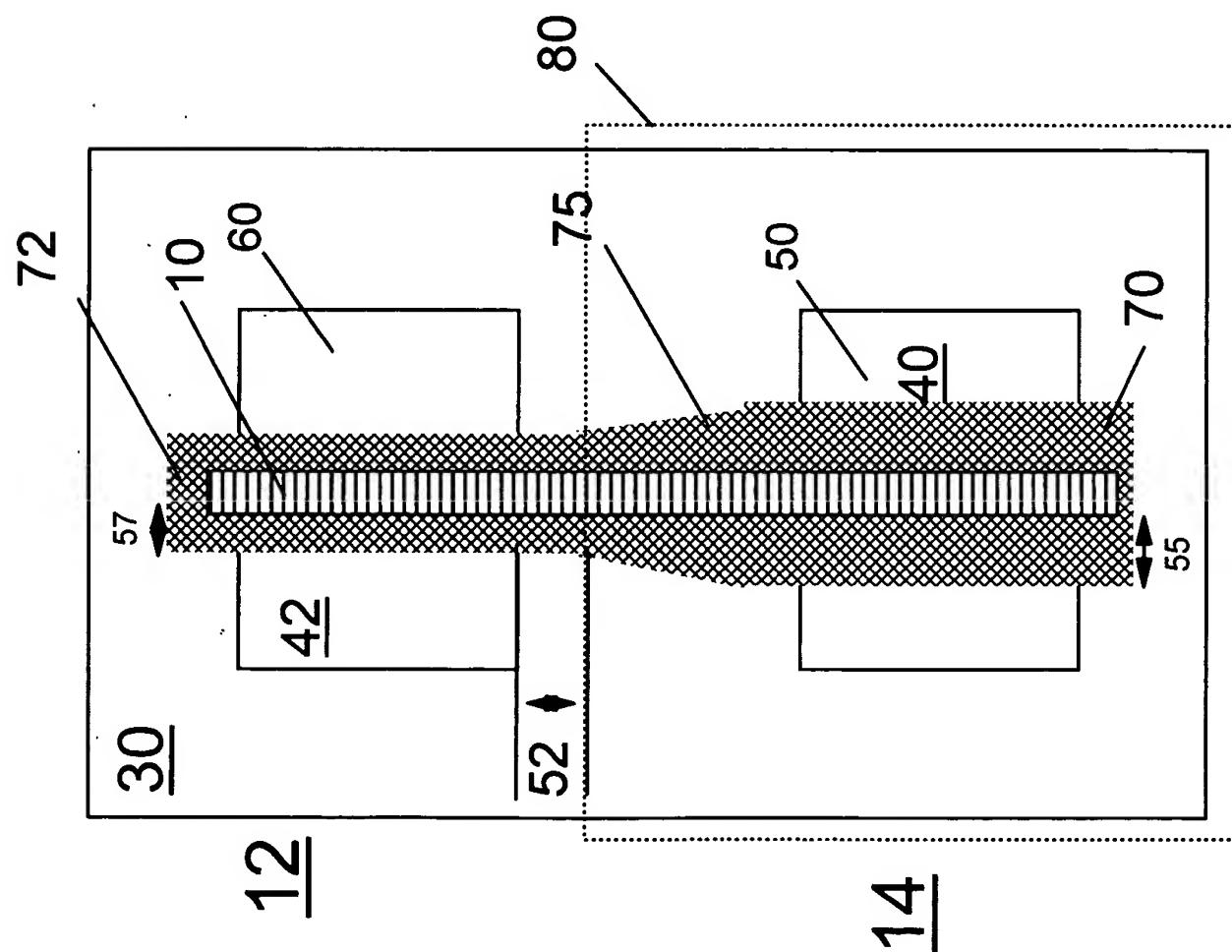


Figure 1B

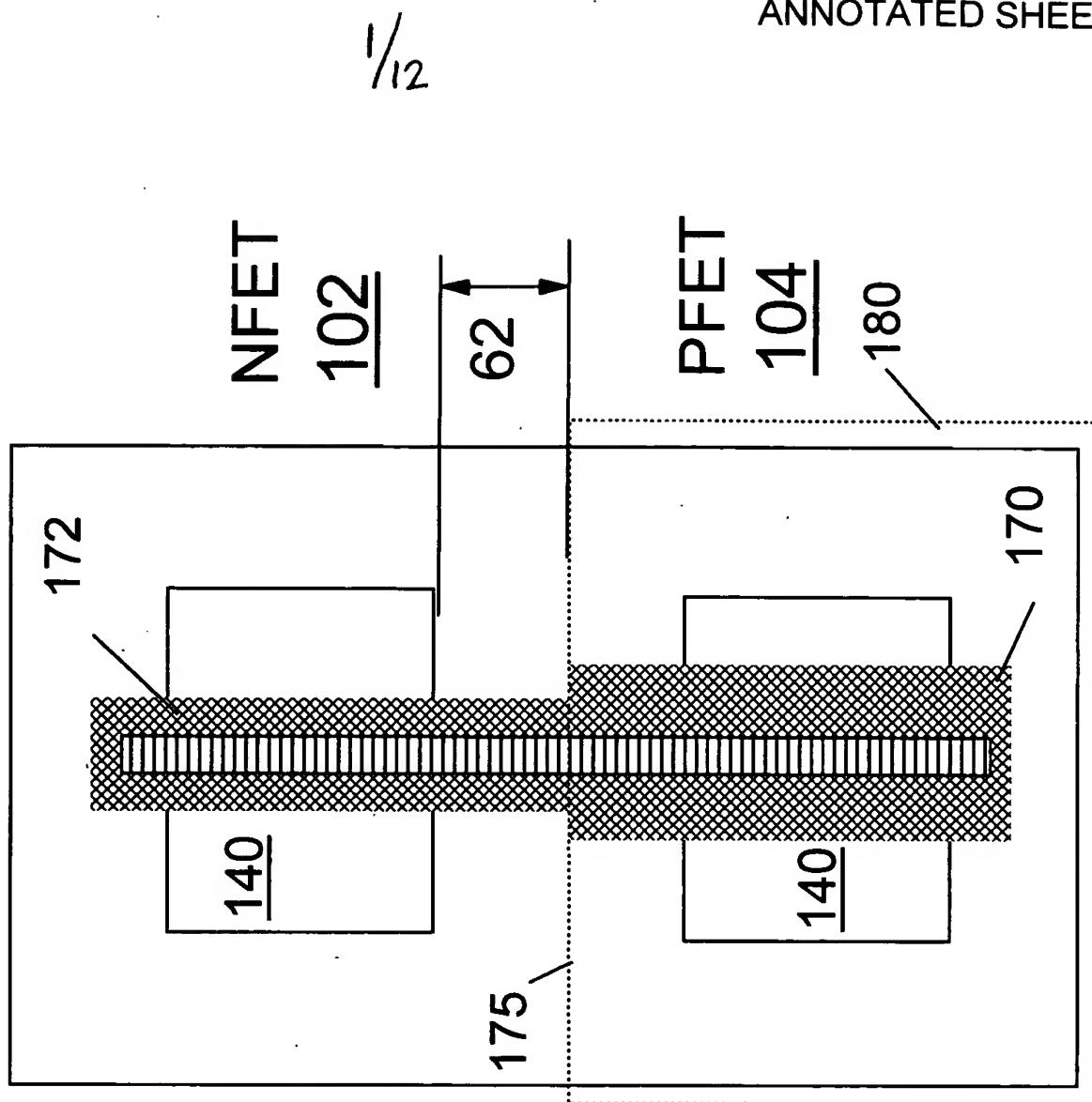


Figure 7

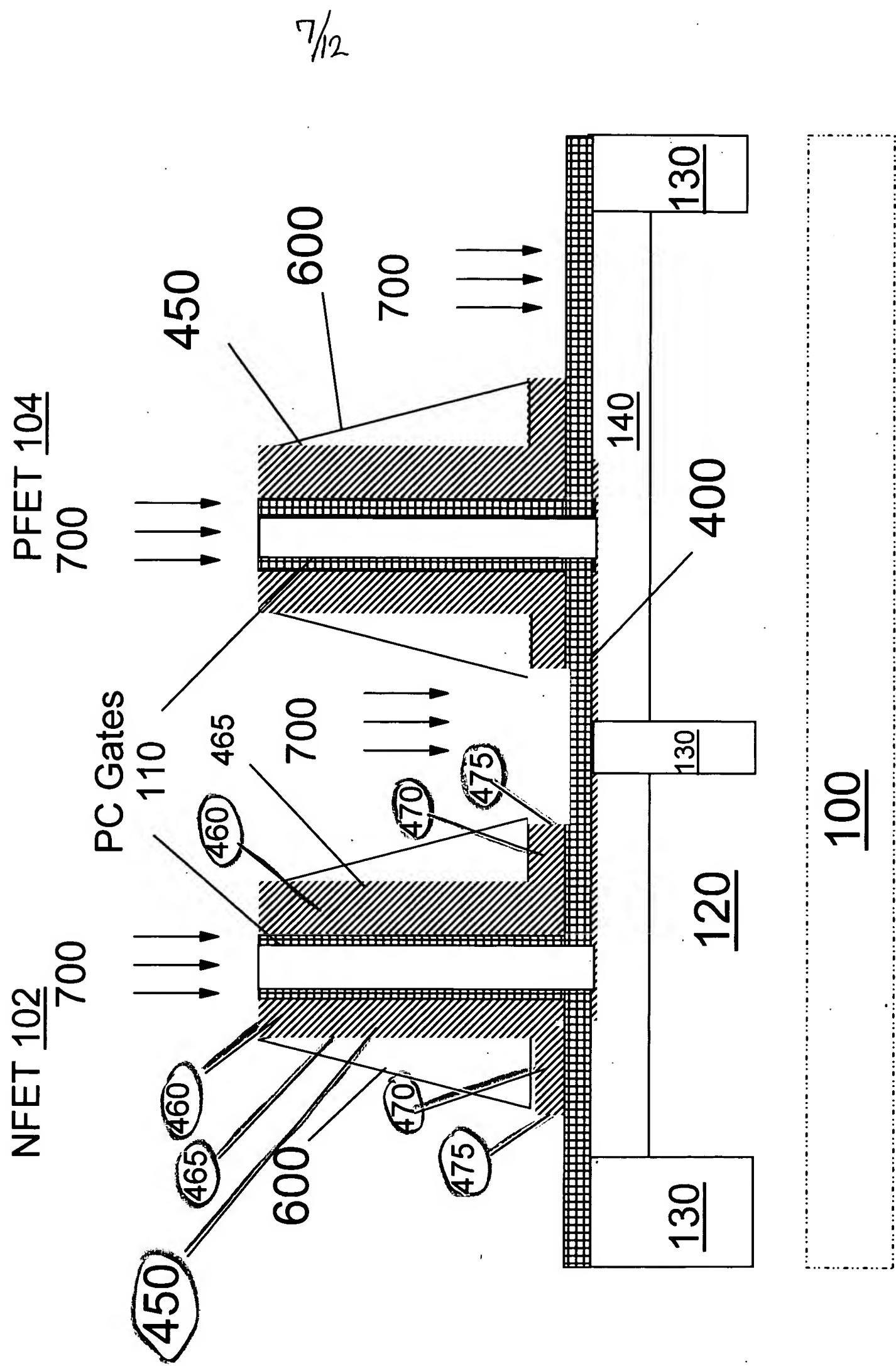


Figure 8

NFET 102PFET 104